Schottky barrier diode
RB480K

●Applications

Low current rectification

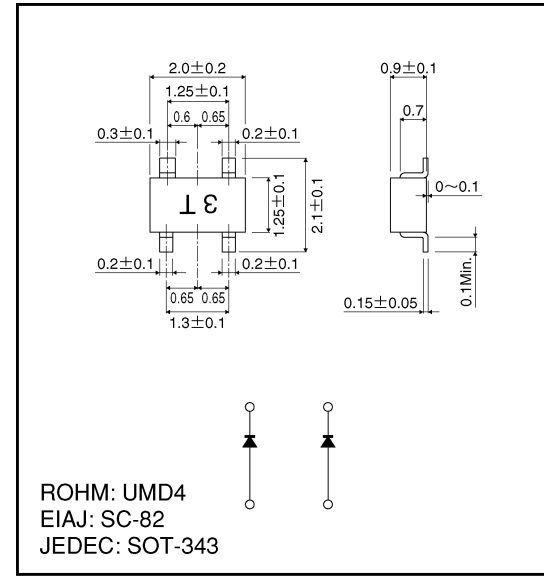
●Features

1) Compact dual element parallel type.
2) High reliability.
3) Low reverse current. (typical capability : 0.3μA)
4) This is a composite component and is ideal for reducing the number of components used.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	45	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	0.1	A
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	Tj	125	℃
Storage temperature	Tstg	−40～+125	℃

*60Hz for 1 ∽

●Electrical characteristics (Ta = 25°C unless specified otherwise)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	—	0.38	0.45	V	I_F=10mA
	V_{F2}	—	0.51	0.60	V	I_F=100mA
Reverse current	I_{R1}	—	0.08	1	μA	V_R=10V
	I_{R2}	—	0.30	5	μA	V_R=40V
Capacitance between terminals	C_{t1}	—	6.0	—	pF	V_R=10V, f=1MHz
	C_{t2}	—	—	25	pF	V_R=0V

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

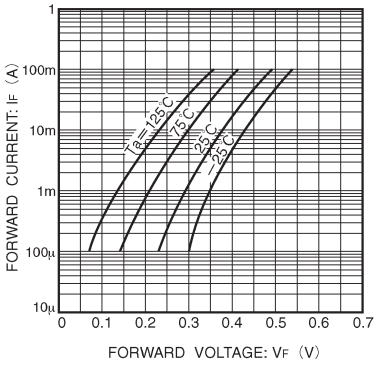


Fig. 1 Forward temperature characteristics

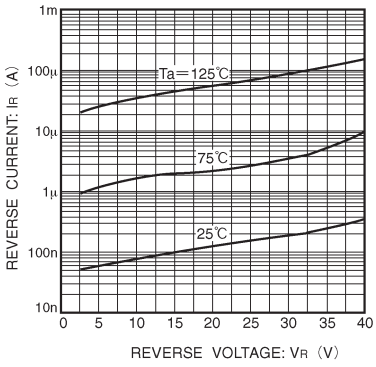


Fig. 2 Reverse temperature characteristics

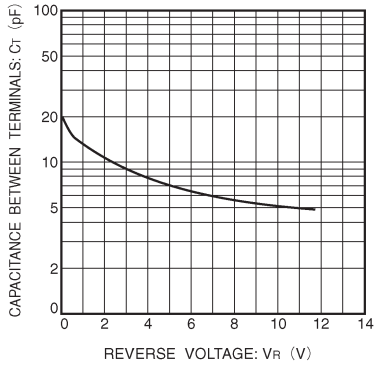


Fig. 3 Capacitance between terminals characteristics

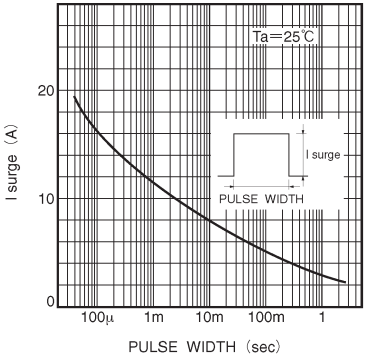


Fig. 4 Surge current characteristics